THE DATASHEET OF

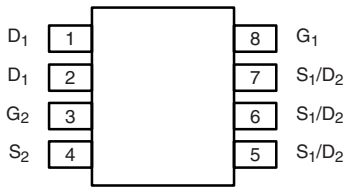
SI4914BDY-T1-E3

Dual N-Channel 30-V (D-S) MOSFET with Schottky Diode

PRODUCT SUMMARY				
	V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)[a]	Q_g (Typ.)
Channel-1	30	0.021 at V_{GS} = 10 V	8.4	6.7
		0.027 at V_{GS} = 4.5 V	7.4	
Channel-2		0.020 at V_{GS} = 10 V	8[d]	7.0
		0.025 at V_{GS} = 4.5 V	8[d]	

SCHOTTKY PRODUCT SUMMARY		
V_{DS} (V)	V_{SD} (V) Diode Forward Voltage	I_F (A)
30	0.50 V at 1.0 A	2.0

SO-8



Top View

Ordering Information: Si4914BDY-T1-E3 (Lead (Pb)-free)
Si4914BDY-T1-GE3 (Lead (Pb)-free and Halogen-free)

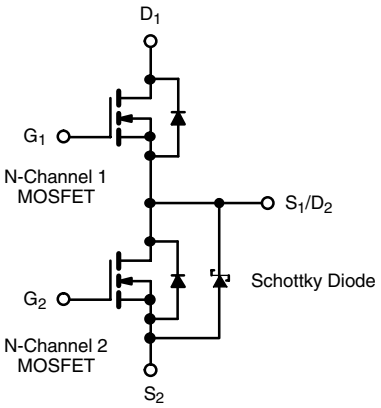
FEATURES

- **Halogen-free According to IEC 61249-2-21 Definition**
- LITTLE FOOT® *Plus* Integrated Schottky
- 100 % R_g and UIS Tested
- Compliant to RoHS Directive 2002/95/EC

Pb-free
RoHS COMPLIANT
HALOGEN FREE Available

APPLICATIONS

- Notebook PC
  - System Power dc-to-dc



ABSOLUTE MAXIMUM RATINGS T_A = 25 °C, unless otherwise noted					
Parameter		**Symbol**	**Channel-1**	**Channel-2**	**Unit**
Drain-Source Voltage		V_{DS}	30		V
Gate-Source Voltage		V_{GS}	20		
Continuous Drain Current (T_J = 150 °C)[a, b]	T_C = 25 °C	I_D	8.4	8[d]	A
	T_C = 70 °C		6.7	7.4	
	T_A = 25 °C		6.7[b, c]	7.4[b, c]	
	T_A = 70 °C		5.3[b, c]	5.7[b, c]	
Pulsed Drain Current (10 µs Pulse Width)		I_{DM}	40	40	
Continuous Source-Drain Diode Current	T_C = 25 °C	I_S	2.4	2.8	
	T_A = 25 °C		1.0[b, c]	1.1[b, c]	
PulseD Source-Drain Current		I_{SM}	40	40	
Single-Pulse Avalanche Current	L = 0.1 mH	I_{AS}	15		
Single-Pulse Avalanche Energy		E_{AS}	11.2		mJ
Maximum Power Dissipation[a, b]	T_C = 25 °C	P_D	2.7	3.1	W
	T_C = 70 °C		1.7	2.0	
	T_A = 25 °C		1.7[b, c]	2.0[b, c]	
	T_A = 70 °C		1.1[b, c]	1.2[b, c]	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 150		°C

Notes:
a. Based on T_C = 25 °C.
b. Surface Mounted on 1" x 1" FR4 board.
c. t = 10 s.
d. Package limited.

THERMAL RESISTANCE RATINGS

Parameter		Symbol	Channel-1		Channel-2		Unit
			Typ.	Max.	Typ.	Max.	
Maximum Junction-to-Ambient[a]	t ≤ 10 s	R_{thJA}	59	70	52	62.5	°C/W
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	36	45	32	40	

Notes:
a. Surface Mounted on 1" x 1" FR4 board.
b. Maximum under Steady State conditions is 120 °C/W for Channel 1 and 115 °C/W for Channel 2.

MOSFET SPECIFICATIONS T_J = 25 °C, unless otherwise noted

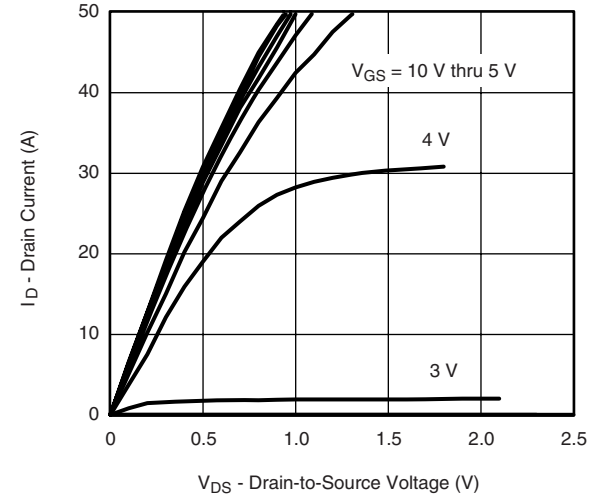
Parameter	Symbol	Test Conditions		Min.	Typ.[a]	Max.	Unit
Static							
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = 250 µA	Ch-1	30			V
			Ch-2	30			
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	I_D = 250 µA	Ch-1		35		mV/°C
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$		Ch-1		- 6.2		
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA	Ch-1	1.2		2.7	V
			Ch-2	1.2		2.7	
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = 20 V	Ch-1			100	nA
			Ch-2			100	
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 30 V, V_{GS} = 0 V	Ch-1			1	µA
			Ch-2			100	
		V_{DS} = 30 V, V_{GS} = 0 V, T_J = 85 °C	Ch-1			15	
			Ch-2			10000	
On-State Drain Current[b]	$I_{D(on)}$	V_{DS} = 5 V, V_{GS} = 10 V	Ch-1	20			A
			Ch-2	20			
Drain-Source On-State Resistance[b]	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 8 A	Ch-1		0.0165	0.021	Ω
		V_{GS} = 10 V, I_D = 8 A	Ch-2		0.0155	0.020	
		V_{GS} = 4.5 V, I_D = 6 A	Ch-1		0.0215	0.027	
		V_{GS} = 4.5 V, I_D = 6 A	Ch-2		0.020	0.025	
Forward Transconductance[b]	g_{fs}	V_{DS} = 15 V, I_D = 8 A	Ch-1		29		S
		V_{DS} = 15 V, I_D = 8 A	Ch-2		33		
Diode Forward Voltage[b]	V_{SD}	I_S = 1.7 A, V_{GS} = 0 V	Ch-1		0.77	1.1	V
		I_S = 1 A, V_{GS} = 0 V	Ch-2		0.46	0.5	
Dynamic[a]							
Total Gate Charge	Q_g	Channel-1 V_{DS} = 15 V, V_{GS} = 4.5 V, I_D = 8 A Channel-2 V_{DS} = 15 V, V_{GS} = 4.5 V, I_D = 8 A	Ch-1		6.7	10.5	nC
			Ch-2		7.0	11.0	
Gate-Source Charge	Q_{gs}		Ch-1		2.8		
			Ch-2		2.8		
Gate-Drain Charge	Q_{gd}		Ch-1		2.0		
			Ch-2		2.0		
Gate Resistance	R_g		Ch-1		2.9	6.0	Ω
			Ch-2		2.0	4.0	

MOSFET SPECIFICATIONS T_J = 25 °C, unless otherwise noted							
Parameter	**Symbol**	**Test Conditions**		**Min.**	**Typ.[a]**	**Max.**	**Unit**
Dynamic[a]							
Turn-On Delay Time	$t_{d(on)}$	Channel-1 V_{DD} = 15 V, R_L = 3 Ω $I_D \cong$ 5 A, V_{GEN} = 10 V, R_g = 1 Ω	Ch-1		9	18	ns
			Ch-2		10	20	
Rise Time	t_r		Ch-1		10	20	
			Ch-2		9	18	
Turn-Off Delay Time	$t_{d(off)}$	Channel-2 V_{DD} = 15 V, R_L = 3 Ω $I_D \cong$ 5 A, V_{GEN} = 10 V, R_g = 1 Ω	Ch-1		16	32	
			Ch-2		16	32	
Fall Time	t_f		Ch-1		9	18	
			Ch-2		8	16	
Source-Drain Reverse Recovery Time	t_{rr}	I_F = 2.2 A, dI/dt = 100 A/µs	Ch-1		35	55	
		I_F = 2.2 A, dI/dt = 100 A/µs	Ch-2		21	35	
Body Diode Reverse Recovery Charge	Q_{rr}	I_F = 2.2 A, dI/dt = 100 A/µs	Ch-1		40		nC
		I_F = 2.2 A, dI/dt = 100 A/µs	Ch-2		11		
Reverse Recovery Fall Time	t_a	I_F = 2.2 A, dI/dt = 100 A/µs	Ch-1		19		ns
		I_F = 2.2 A, dI/dt = 100 A/µs	Ch-2		11		
Reverse Recovery Rise Time	t_b	I_F = 2.2 A, dI/dt = 100 A/µs	Ch-1		16		
		I_F = 2.2 A, dI/dt = 100 A/µs	Ch-2		10		

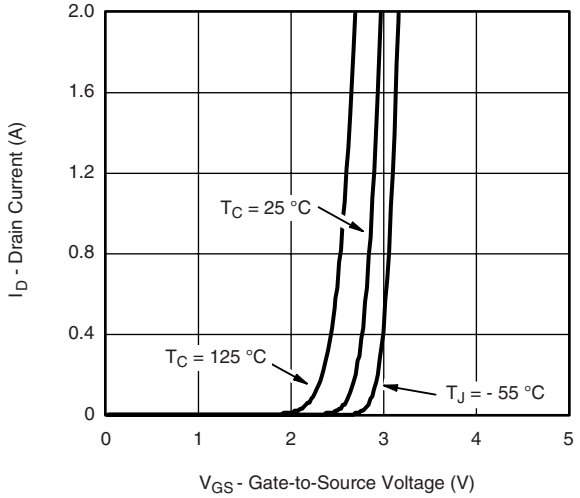
Notes:
a. Guaranteed by design, not subject to production testing.
b. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

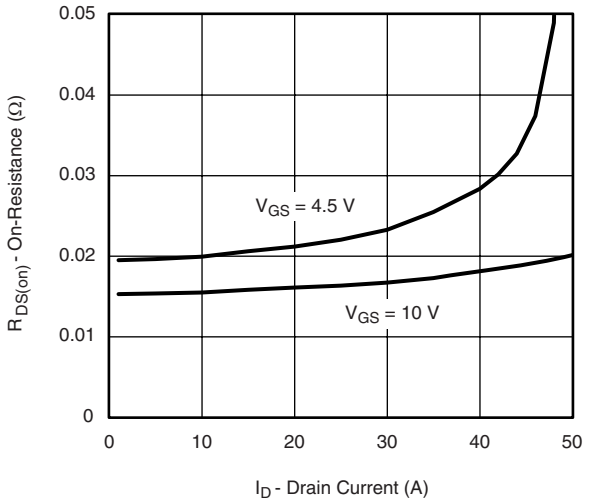
CHANNEL-1 TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



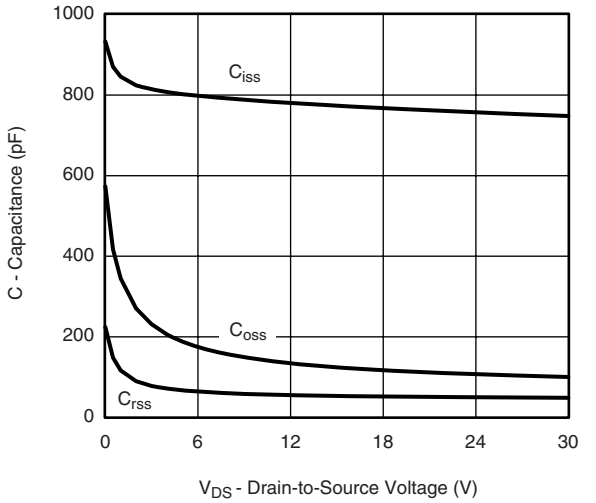
Output Characteristics



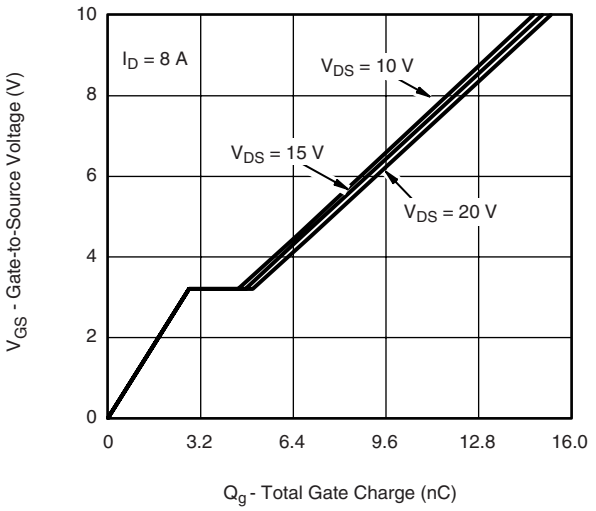
Transfer Characteristics



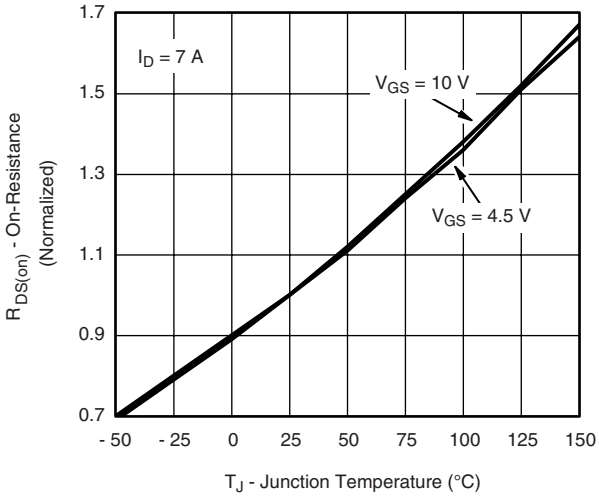
On-Resistance vs. Drain Current



Capacitance

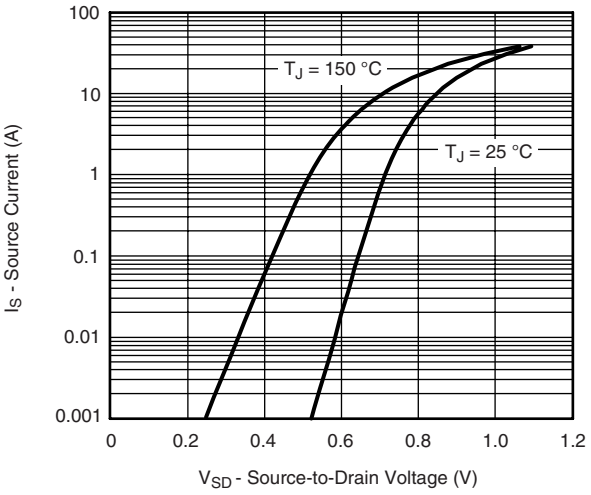


Gate Charge

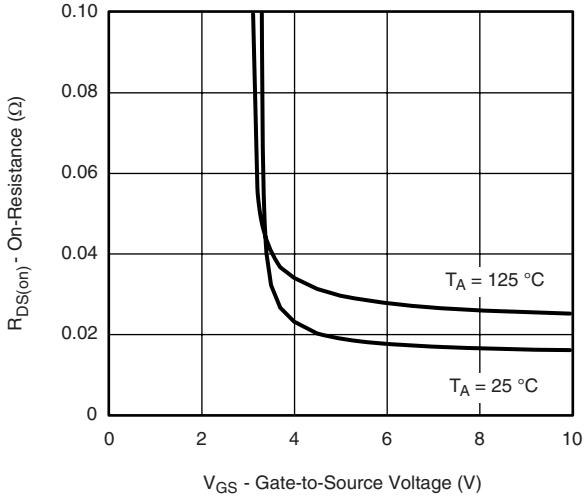


On-Resistance vs. Junction Temperature

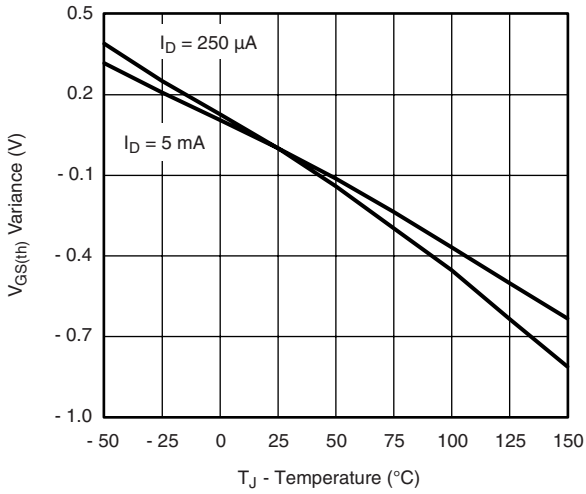
CHANNEL-1 TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



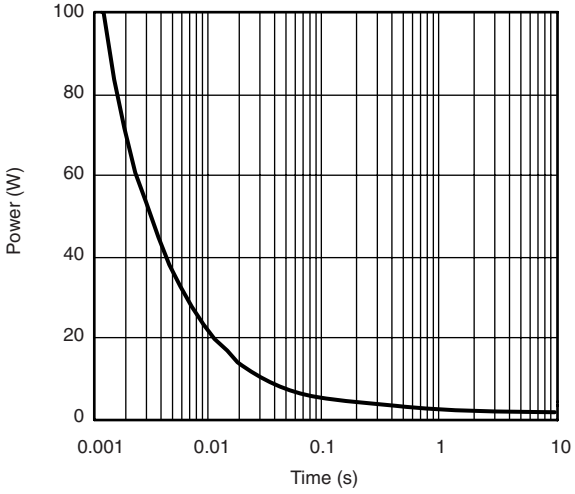
Source-Drain Diode Forward Voltage



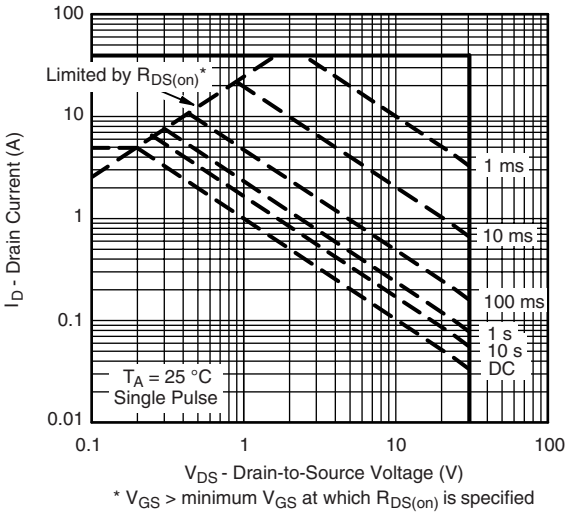
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



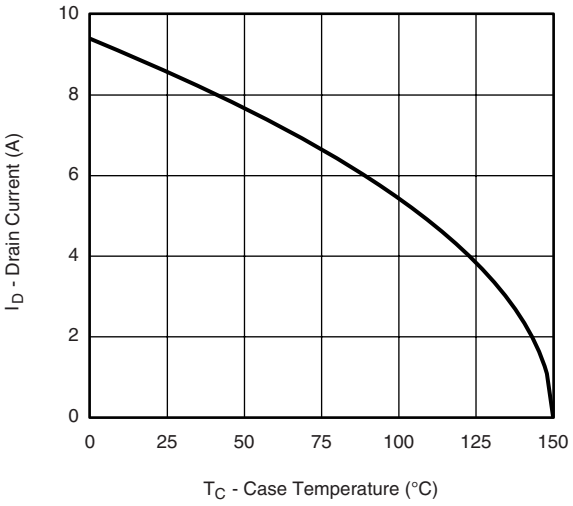
Single Pulse Power, Junction-to-Ambient



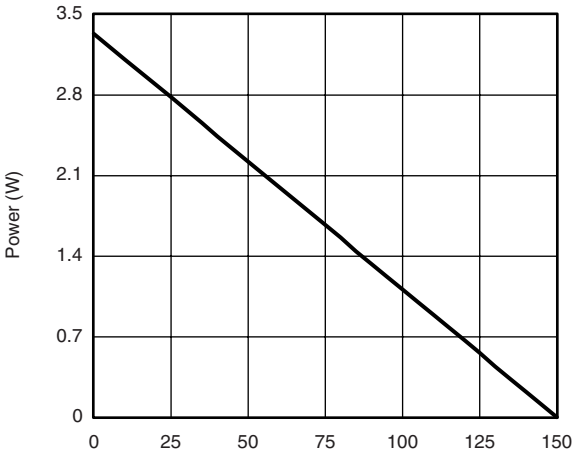
* V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area

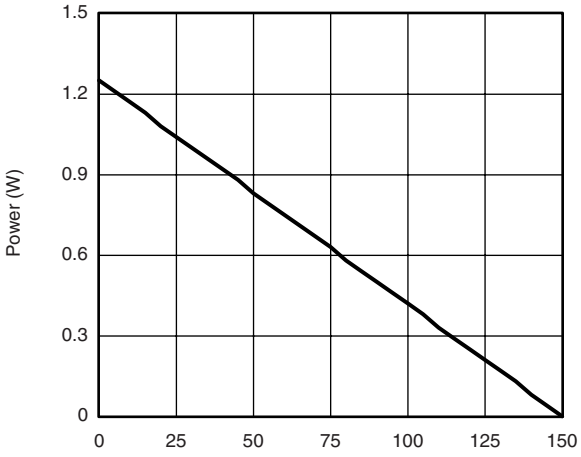
CHANNEL-1 TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Current Derating*



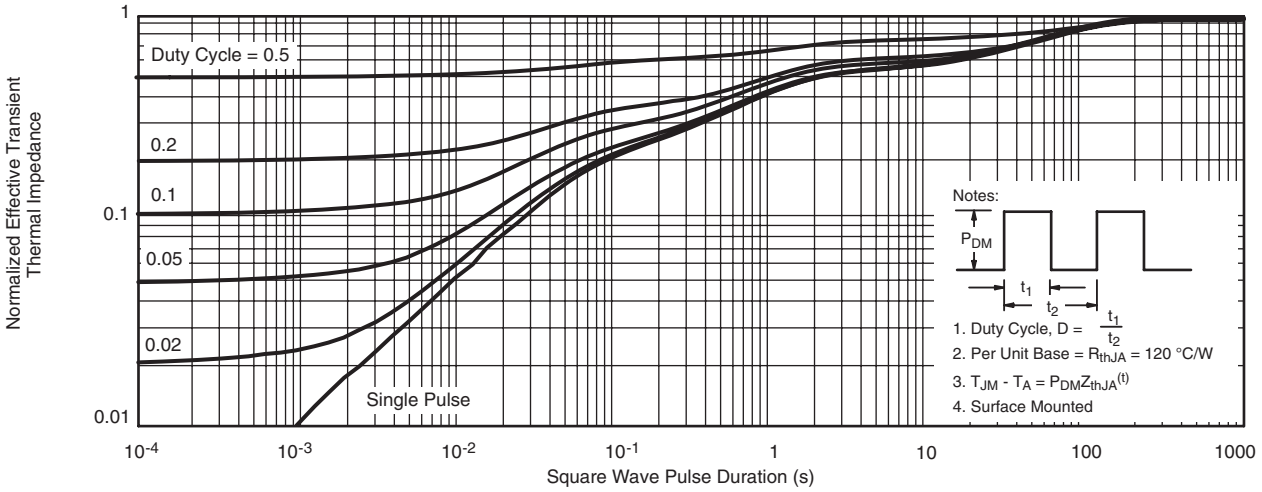
Power, Junction-to-Foot



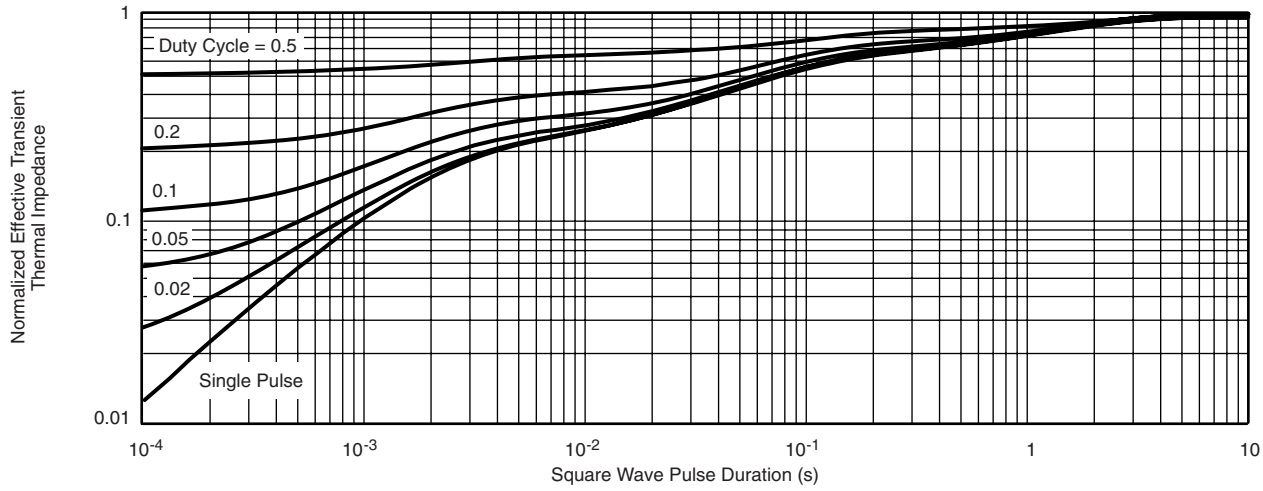
Power, Junction-to-Ambient

* The power dissipation P_D is based on $T_{J(max)}$ = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

CHANNEL-1 TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

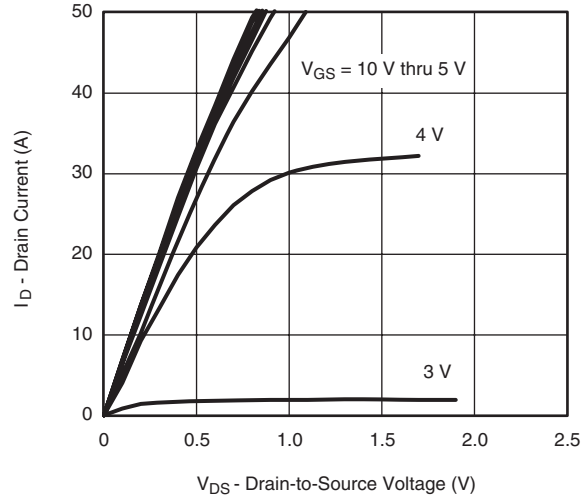


Normalized Thermal Transient Impedance, Junction-to-Ambient

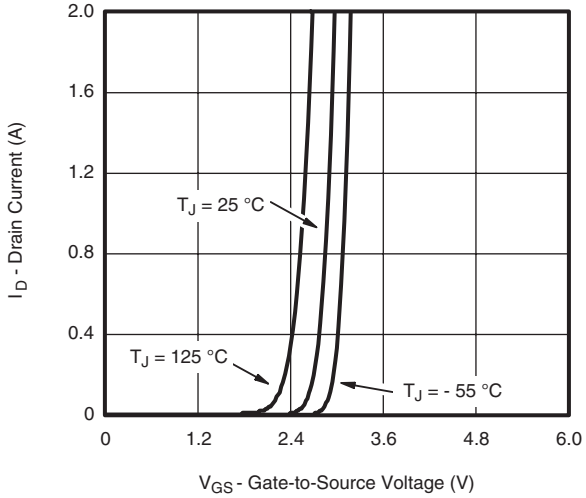


Normalized Thermal Transient Impedance, Junction-to-Foot

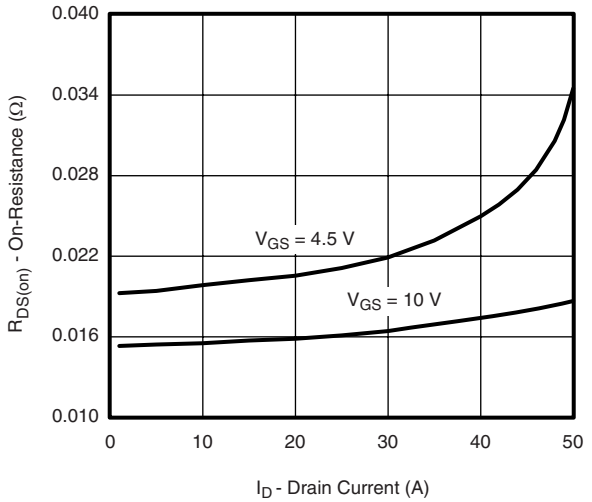
CHANNEL-2 TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



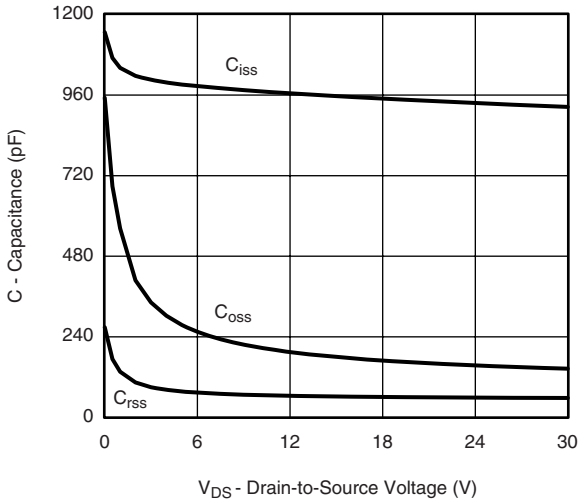
Output Characteristics



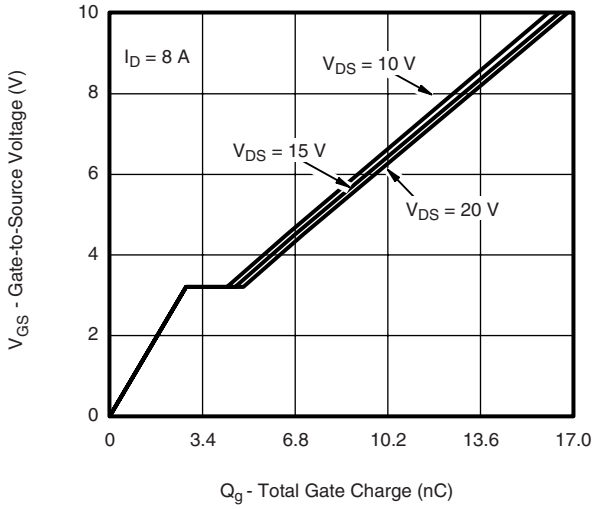
Transfer Characteristics



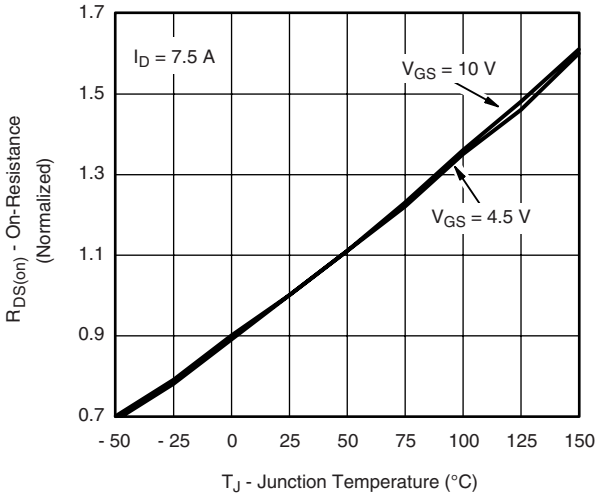
On-Resistance vs. Drain Current



Capacitance

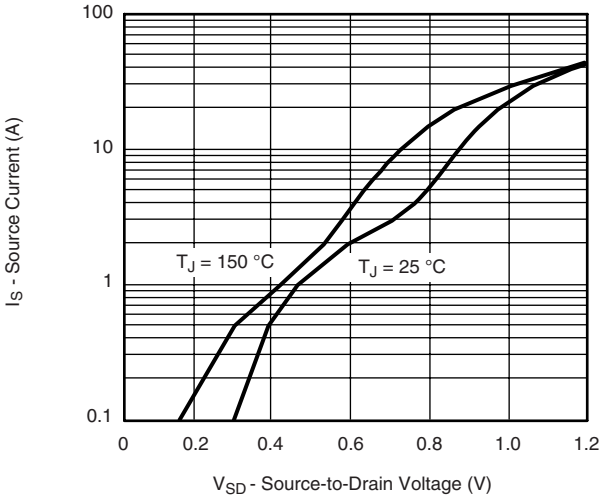


Gate Charge

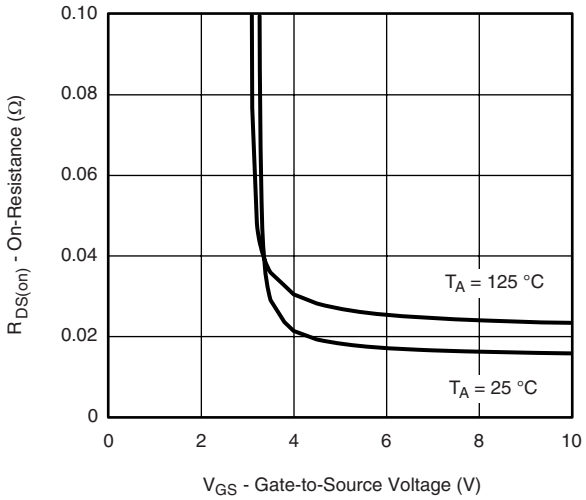


On-Resistance vs. Junction Temperature

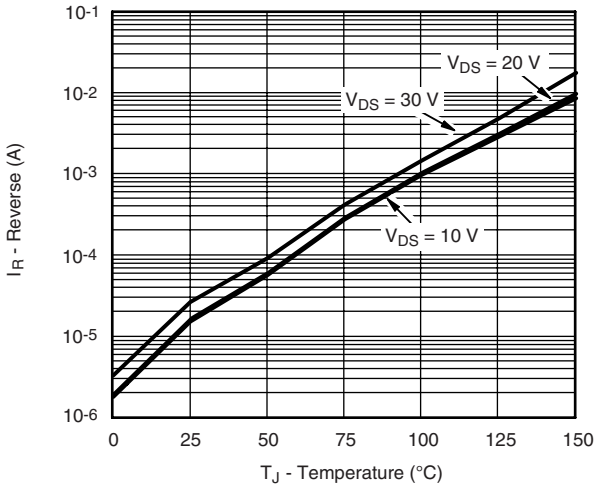
CHANNEL-2 TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



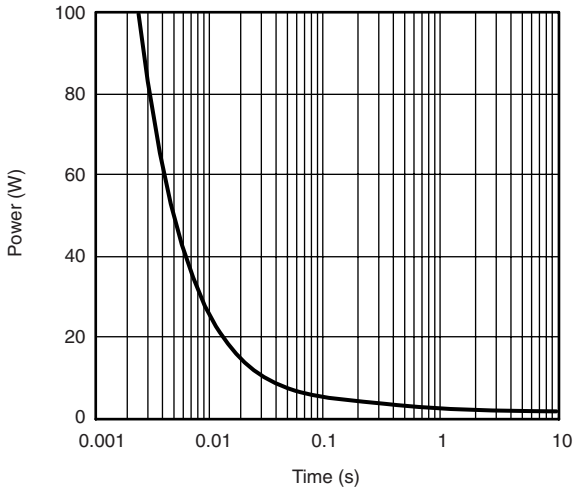
Source-Drain Diode Forward Voltage



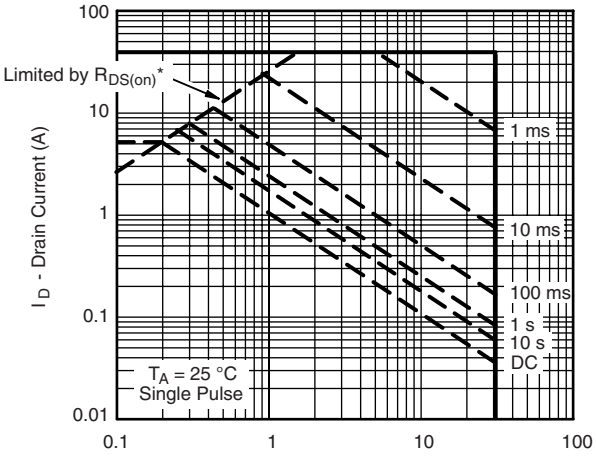
On-Resistance vs. Gate-to-Source Voltage



Reverse Current Schottky



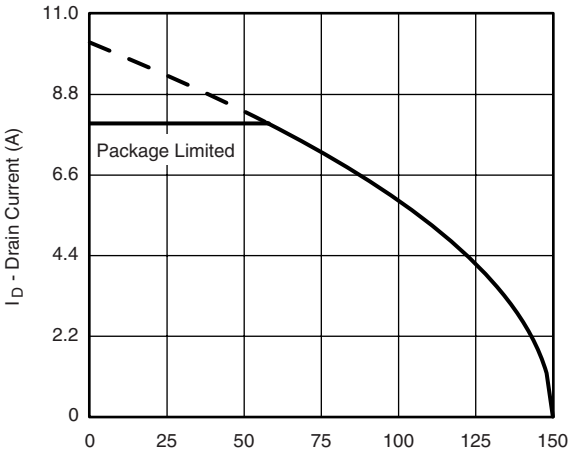
Single Pulse Power, Junction-to-Ambient



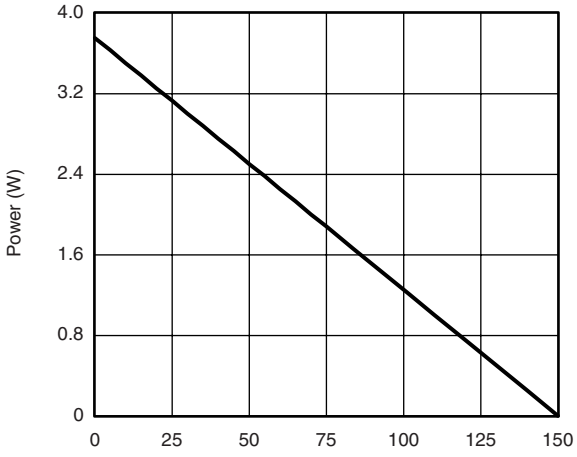
* V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area

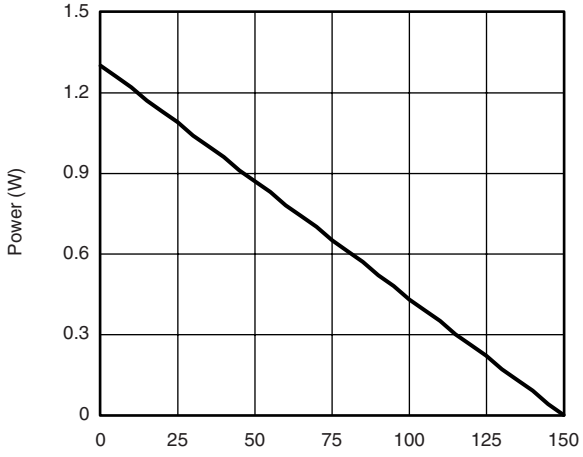
CHANNEL-2 TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Current Derating*



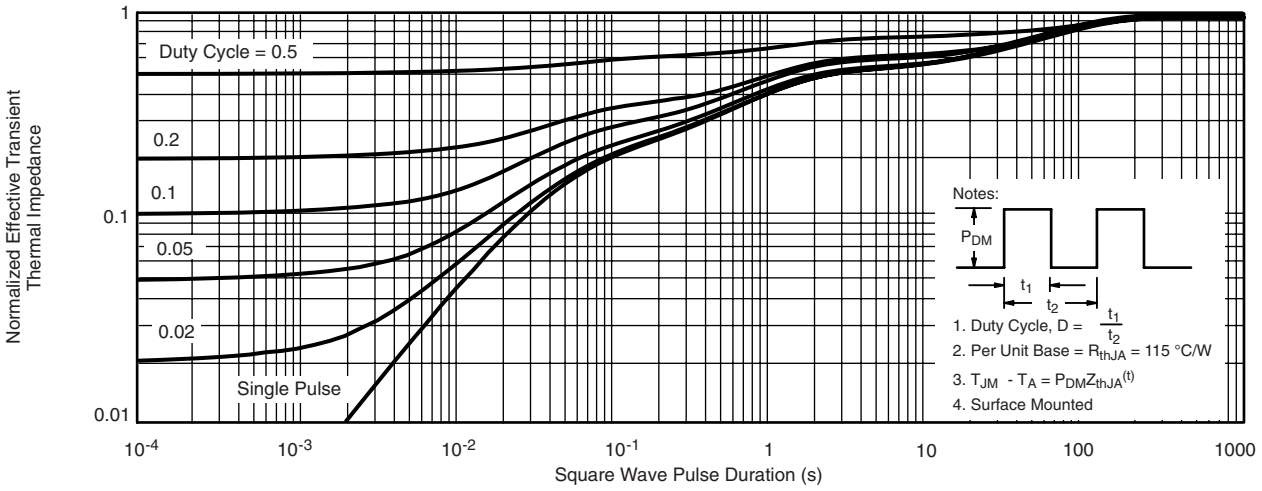
Power, Junction-to-Foot



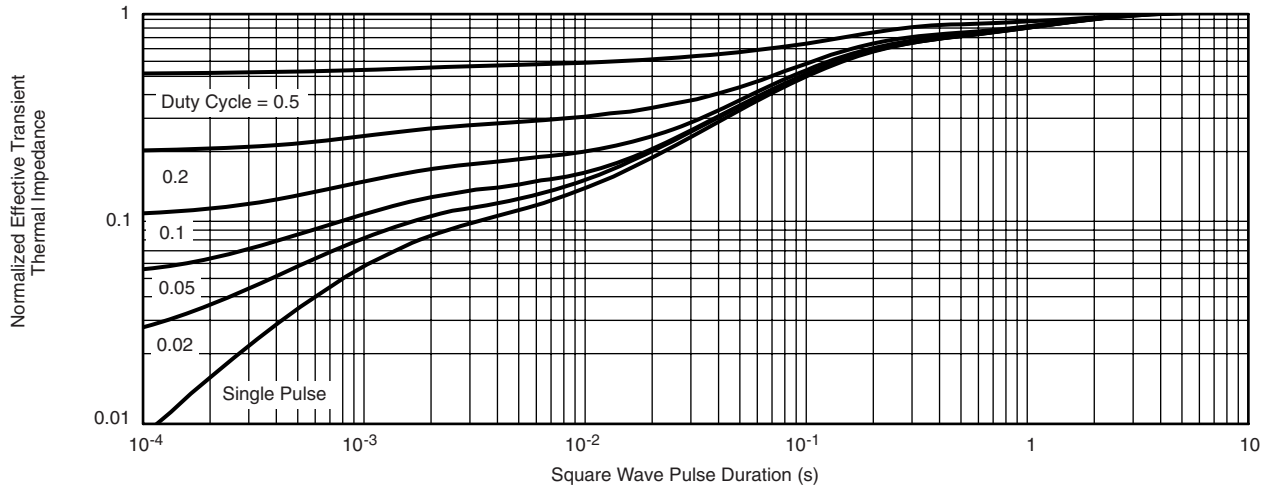
Power, Junction-to-Ambient

* The power dissipation P_D is based on $T_{J(max)}$ = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

CHANNEL-2 TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



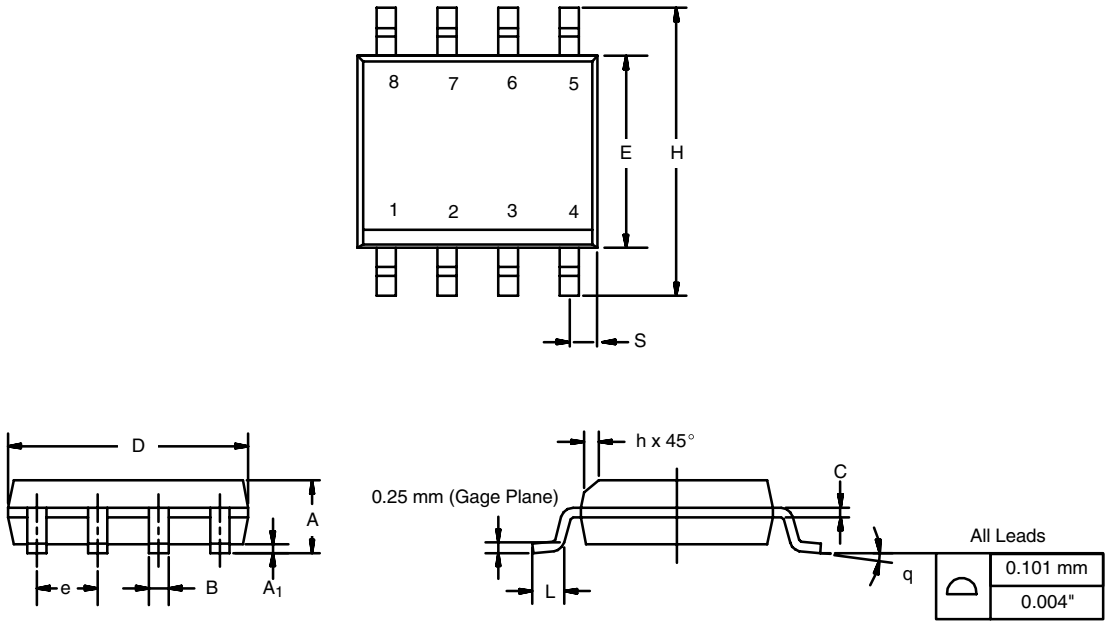
Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

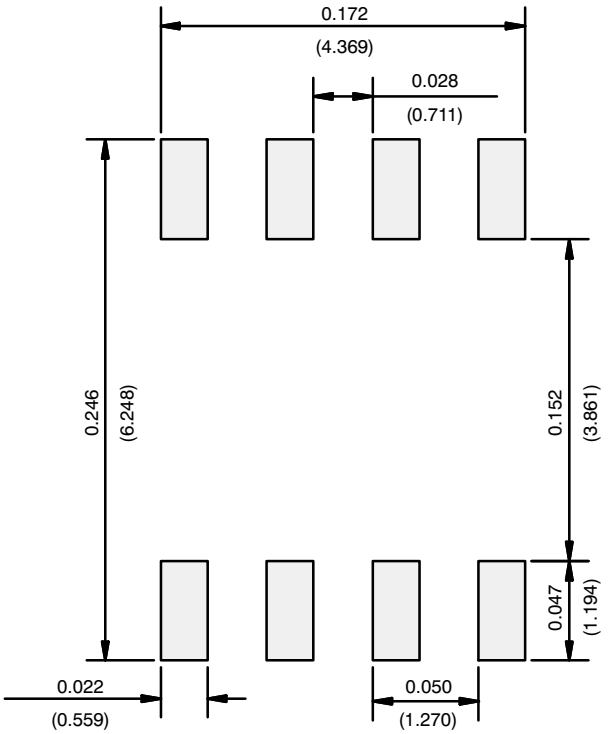
Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?69654.

SOIC (NARROW): 8-LEAD
JEDEC Part Number: MS-012



DIM	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	1.35	1.75	0.053	0.069
A_1	0.10	0.20	0.004	0.008
B	0.35	0.51	0.014	0.020
C	0.19	0.25	0.0075	0.010
D	4.80	5.00	0.189	0.196
E	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
H	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.020
L	0.50	0.93	0.020	0.037
q	0°	8°	0°	8°
S	0.44	0.64	0.018	0.026
ECN: C-06527-Rev. I, 11-Sep-06 DWG: 5498				

RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads
Dimensions in Inches/(mm)

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